

FIG. 6 (PRIOR ART)

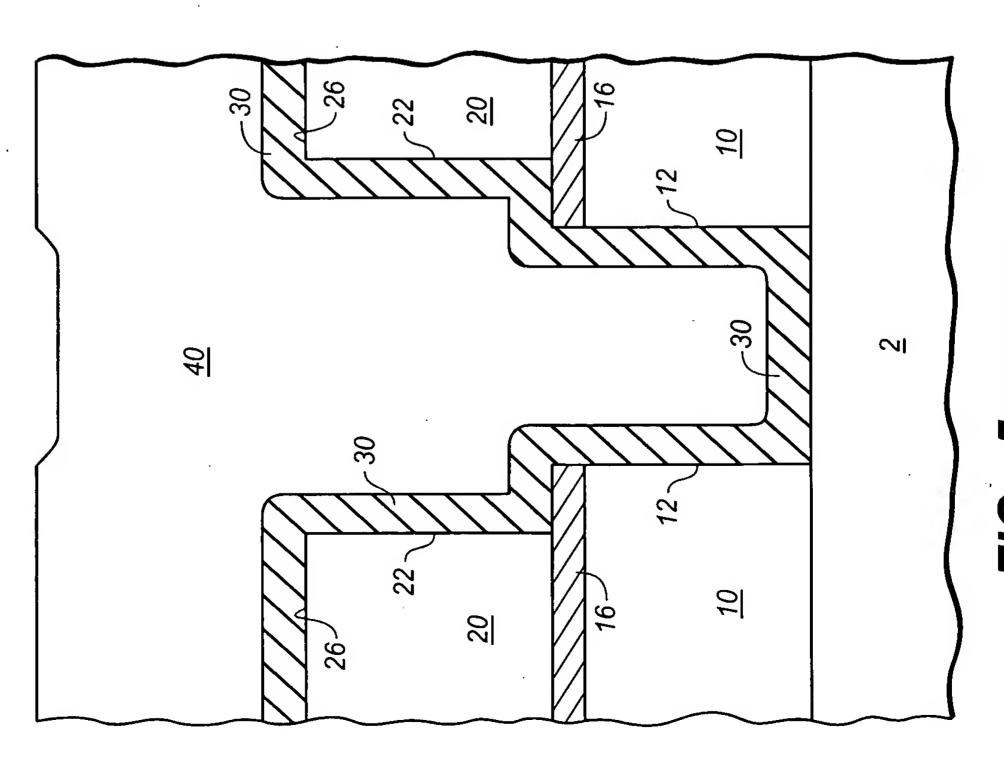
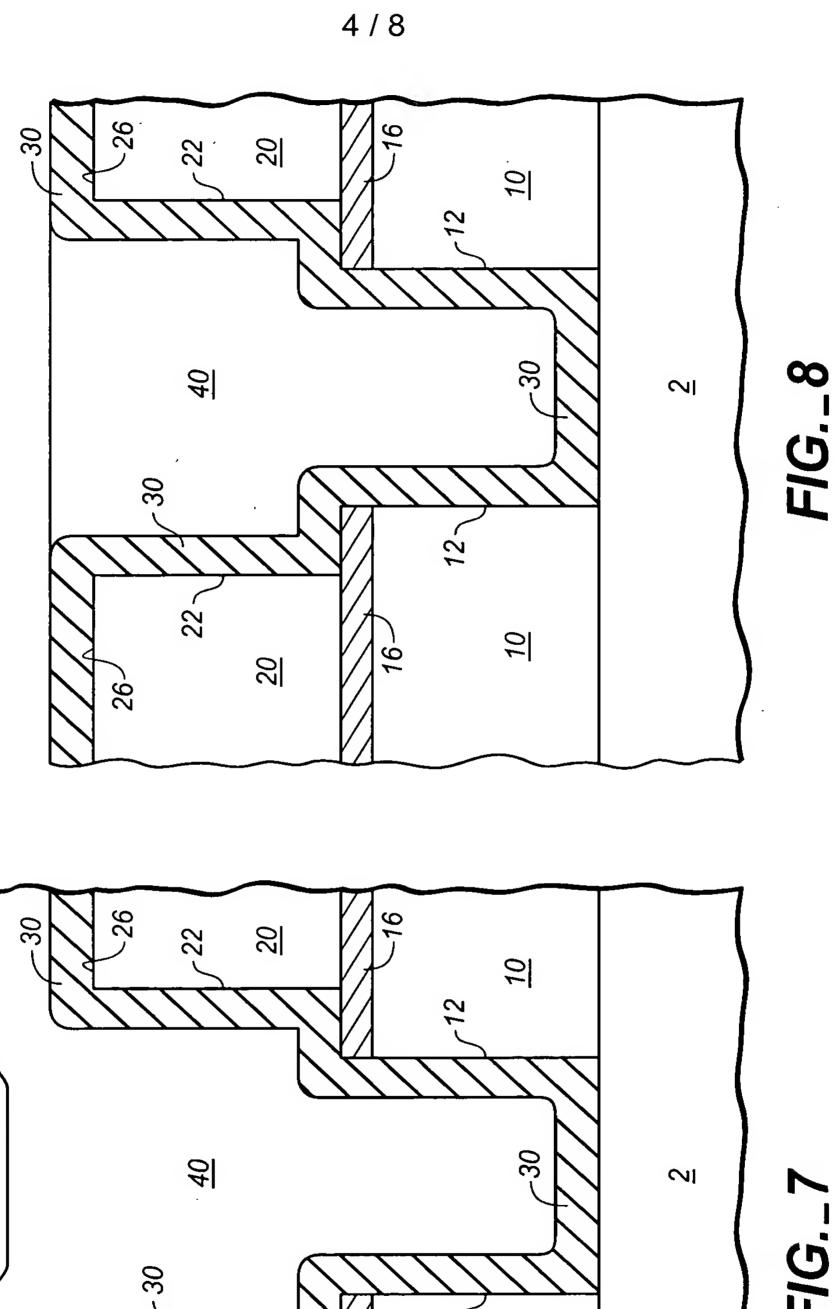


FIG. 5 (PRIOR ART)

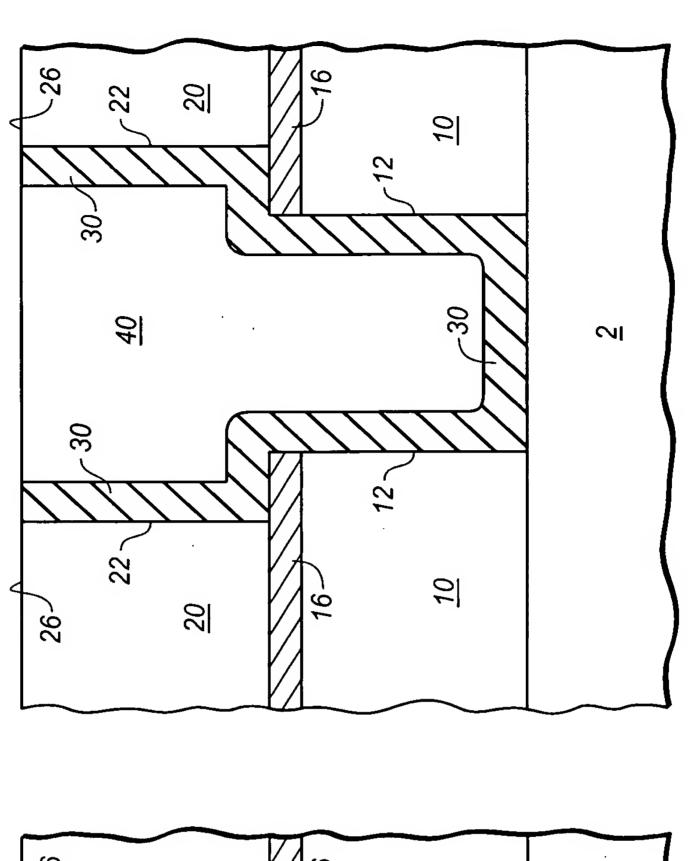




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Line Walls of Opening in Layer of Dielectric Material of Integrated Circuit Structure with Barrier Material

Fill Lined Opening in Layer of Dielectric Material with Copper Filler Material

Then Remove from About \_\_\_\_\_% to About\_\_\_\_\_% of the Excess Copper on Barrier Layer Material Over Top Surface of Layer of Dielectric Material by Chemical Mechanical Polishing

Then Remove Remaining Copper on Barrier Layer Material Over Top Surface of Layer of Dielectric Material by Electropolishing

Then Remove Excess Barrier Layer Material Over Top Surface of Layer of Dielectric Material by Dry Etching with

## FIG.\_10

Etch System Selective to Copper and Dielectric Material

Line Walls of Opening in Layer of Dielectric Material of Integrated Circuit Structure with Barrier Material

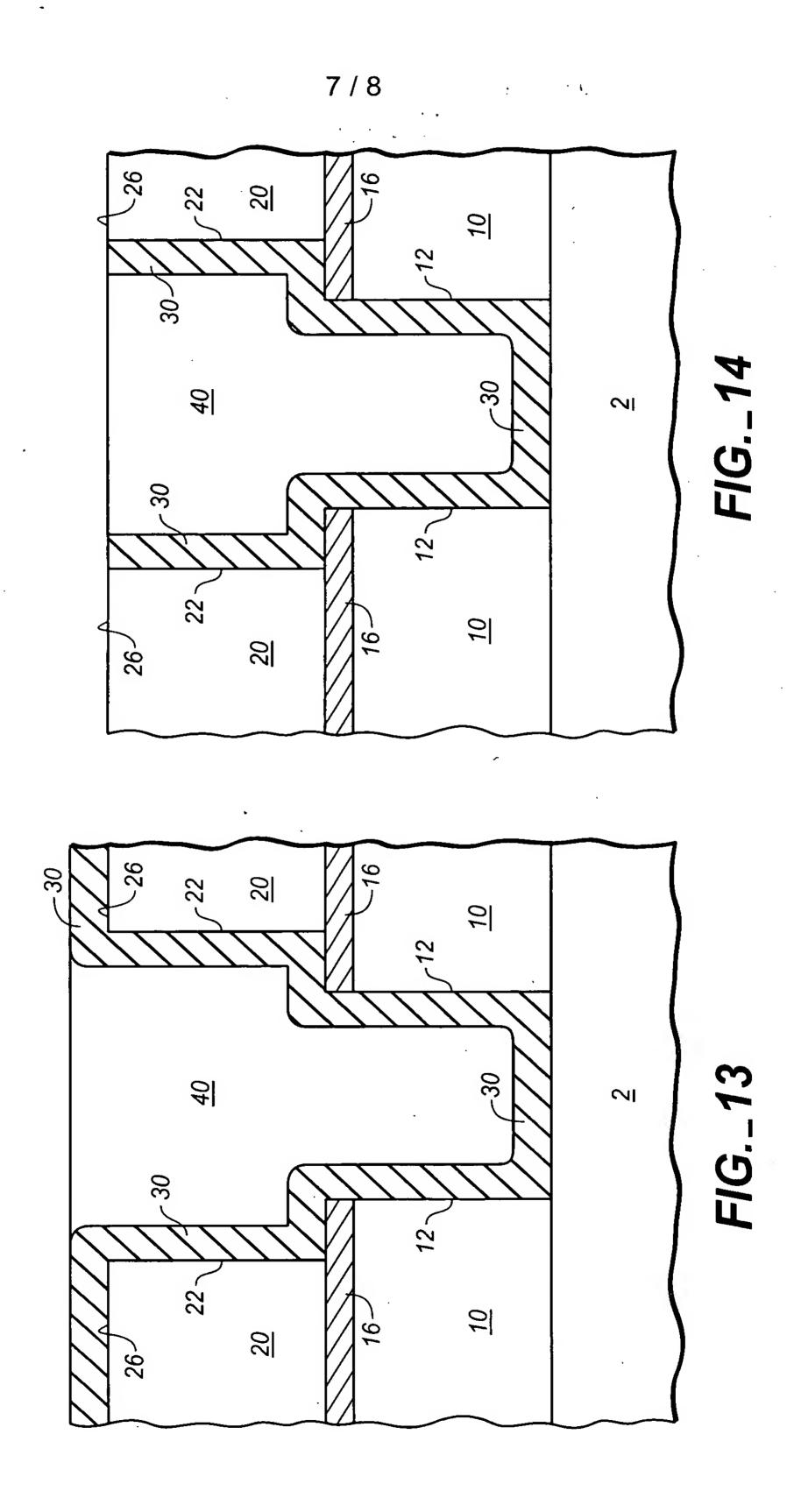
Fill Lined Opening in Layer of Dielectric Material with Copper Filler Material

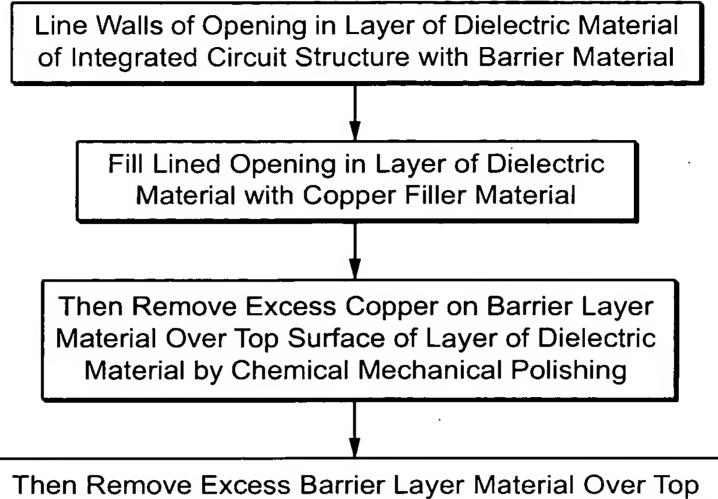
Then Remove Excess Copper on Barrier Layer Material Over Top Surface of Layer of Dielectric Material by Electropolishing

Then Remove Excess Barrier Layer Material Over Top Surface of Layer of Dielectric Material by Dry Etching with

FIG.\_12

Etch System Selective to Copper and Dielectric Material





Surface of Layer of Dielectric Material by Dry Etching with Etch System Selective to Copper and Dielectric Material

FIG.\_15